

Precision 8-Ch/Dual 4-Ch Low Voltage Analog Multiplexers

DESCRIPTION

The DG9408, DG9409 uses BiCMOS wafer fabrication technology that allows the DG9408, DG9409 to operate on single and dual supplies. Single supply voltage ranges from 3 V to 12 V while dual supply operation is recommended with $\pm 3 \text{ V}$ to $\pm 6 \text{ V}$.

The DG9408 is an 8-channel single-ended analog multiplexer designed to connect one of eight inputs to a common output as determined by a 3-bit binary address (A_0, A_1, A_2) . The DG9409 is a dual 4-channel differential analog multiplexer designed to connect one of four differential inputs to a common dual output as determined by its 2-bit binary address (A_0, A_1) . Break-before-make switching action to protect against momentary crosstalk between adjacent channels.

As a committed partner to the community and the environment, Vishay Siliconix manufactures this product with lead (Pb)-free device terminations. The DG9408, DG9409 are offered in a QFN package that has a nickel-palladium-gold device terminations and is represented by the lead (Pb)-free "-E4" suffix. The nickel-palladium-gold device terminations meet all the JEDEC standards for reflow and MSL ratings.

FEATURES

- 2.7 V to 12 V single supply or ± 3 V to ± 6 V dual supply operation
- Low on-resistance R_{ON} : 3.9 Ω typ.
- Fast switching: t_{ON} 42 ns, t_{OFF} 24 ns
- Break-before-make guaranteed
- Low leakage
- TTL, CMOS, LV logic (3 V) compatible
- 2000 V ESD protection (HBM)
- Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>

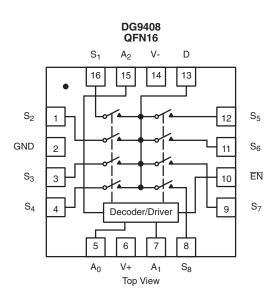
BENEFITS

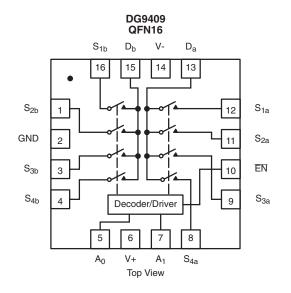
- High accuracy
- Single and dual power rail capacity
- Wide operating voltage range
- Simple logic interface

APPLICATIONS

- Data acquisition systems
- · Battery operated equipment
- Portable test equipment
- Sample and hold circuits
- Communication systems
- SDSL, DSLAM
- Audio and video signal routing

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION





Pb-free

ROHS COMPLIANT HALOGEN



TRUTH TABLES AND ORDERING INFORMATION

TRUTI	TRUTH TABLE DG9408								
A ₂	A ₁	A ₀	EN	On Switch					
Х	Х	Х	1	None					
0	0	0	0	1					
0	0	1	0	2					
0	1	0	0	3					
0	1	1	0	4					
1	0	0	0	5					
1	0	1	0	6					
1	1	0	0	7					
1	1	1	0	8					

TRUTH TABLE DG9409								
A ₁	A ₀	EN	On Switch					
Х	Х	1	None					
0	0	0	1					
0	1	0	2					
1	0	0	3					
1	1	0	4					

X = Don't care

For low and high voltage levels for V_{AX} and V_{EN} consult "Digital Control" Parameters for Specific V+ operation. See Specifications Tables for:

Single Supply 12 V Dual Supply V+ = 5 V, V- = - 5 V Single Supply 5 V Single Supply 3 V

ORDERING INFORMATION							
Temp. Range	Package	Part Number					
- 40 °C to 85 °C	16-pin QFN (4 mm x 4 mm)	DG9408DN-T1-E4					
- 40 0 10 85 0	(Variation 1)	DG9409DN-T1-E4					

Parameter		Limit	Unit	
Voltage Referenced V+ to V-		14		
GND		7		
Digital Inputs ^a , V _S , V _D	(V-) - 0.3 to (V+) + 0.3			
Current (Any Terminal Except S or D)	30			
Continuous Current, S or D		100	mA	
Peak Current, S or D (Pulsed at 1 ms, 10 % Duty Cycle max.)		200		
Package Solder Reflow Conditions ^d	240	°C		
Storage Temperature		- 65 to 150	1	
Power Dissipation (Package) ^b , ($T_A = 70 \ ^{\circ}C$)	16-pin (4 x 4 mm) QFN ^c	1880	mW	

Notes:

a. Signals on SX, DX or INX exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings.

b. All leads soldered or welded to PC board.

c. Derate 23.5 mW/°C above 70 °C.

d. Manual soldering with soldering iron is not recommended for leadless components. The QFN is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper lip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.



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SPECIFICATIONS (Sin	igle Supply	/ 12 V)						
	Test Conditions Unless Otherwise Specified V+ = 12 V, ± 10 %, V- = 0 V			- 40	Limits 0 °C to 85	°C		
Parameter	Symbol	V _A , V _{EN} = 0.8 V or 2.4 V		Temp. ^b	Min. ^c	Typ. ^d	Max. ^c	Unit
Analog Switch	-							
Analog Signal Range ^e	V _{ANALOG}			Full	0		12	V
On-Resistance	R _{ON}	V+ = 10.8 V, V_D = 2 V or 9 V, I_S = sequence each switch or		Room Full		4	7 7.5	
R _{ON} Match Between Channels ^g	ΔR_{ON}			Room			3.6	Ω
On-Resistance Flatness ⁱ	R _{ON} Flatness	V+ = 10.8 V, V _D = 2 V or 9 V, I _S =	= 50 mA	Room			8	
Switch Off Leakage Current	I _{S(off)}	V _{EN} = 2.4 V, V _D = 11 V or 1 V, V _S =	1 V or 11 V	Room Full	- 2 - 15		2 15	
	I _{D(off)}	······································		Room Full	- 2 - 15		2 15	nA
Channel On Leakage Current	I _{D(on)}	$V_{\overline{EN}} = 0 V, V_{S} = V_{D} = 1 V \text{ or } 11 V$		Room Full	- 2 - 15		2 15	
Digital Control		-			-	-	_	
Logic High Input Voltage	V _{INH}	-		Full	2.4			v
Logic Low Input Voltage	V _{INL}			Full			0.8	
Input Current	I _{IN}	$V_{AX} = V_{\overline{EN}} = 2.4 \text{ V or } 0.8 \text{ V}$		Full	- 1		1	μA
Dynamic Characteristics				Г	r	r	r	
Transition Time	t _{TRANS}	V _{S1} = 8 V, V _{S8} = 0 V, (DG94 V _{S1b} = 8 V, V _{S4b} = 0 V, (DG9- see fig. 2		Room Full		42	71 75	
Break-Before-Make Time	t _{BBM}	V _{S(all)} = V _{DA} = 5 V see fig. 4		Room Full	2	24		ns
Enable Turn-On Time	t _{ON(EN)}	V _{AX} = 0 V, V _{S1} = 5 V (DG94 V _{AX} = 0 V, V _{S1b} = 5 V (DG94		Room Full		42	70 75	
Enable Turn-Off Time	$t_{OFF(\overline{EN})}$	see fig. 3		Room Full		24	44 46	
Charge Injection ^e	Q	$C_L = 1 \text{ nF}, V_{GEN} = 0 \text{ V}, R_{GEN} =$	= 0 Ω	Room		29		рС
Off Isolation ^{e, h}	OIRR	f = 100 kHz, R _L = 1 kΩ		Room		- 80		dB
Crosstalk ^e	X _{TALK}	1 = 100 M12, HL = 1 M22		Room		- 85		uБ
Source Off Capacitance ^e	C _{S(off)}	f = 1 MHz, $V_S = 0$ V, $V_{\overline{EN}} = 2.4$ V	DG9408 DG9409	Room Room		21 23		
Drain Off Capacitance ^e	C _{D(off)}	f = 1 MHz, V_D = 0 V, $V_{\overline{EN}}$ = 2.4 V	DG9408 DG9409	Room Room		211 112		pF
Drain On Capacitance ^e	C _{D(on)}	$f = 1 \text{ MHz}, \text{ V}_{\text{D}} = 0 \text{ V}, \text{ V}_{\overline{\text{EN}}} = 0 \text{ V}$	DG9408 DG9409	Room Room		238 137		
Power Supplies		I	2 00 100			107	l	
Power Supply Current	l+	V _{EN} = V _A = 0 V or V+		Room			1	μA
				1				

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SPECIFICATIONS (Du	al Supply '	V+ = 5 V, V- = - 5 V)						
		Test Conditions Unless Otherwise Specified $V+ = 5 V, V- = -5 V, \pm 10 \%$ $V_A, V_{\overline{EN}} = 0.8 V \text{ or } 2 V^{f}$			- 40	Limits) °C to 85	5 °C	
Parameter	Symbol			Temp. ^b	Min. ^c	Typ. ^d	Max. ^c	Unit
Analog Switch		•						
Analog Signal Range ^e	V _{ANALOG}			Full	- 5		5	V
On-Resistance	R _{ON}	V+ = 4.5 V, V- = - 4.5 V, V _D = \pm 3.5 V, sequence each switch on	-	Room Full		5	8 8.5	
R _{ON} Match Between Channels ^g	ΔR_{ON}			Room			3.6	Ω
On-Resistance Flatness ⁱ	R _{ON} Flatness	V+ = 4.5 V, V- = - 4.5 V, V _D = ± 3.5 V,	I _S = 50 mA	Room			8.2	
Switch Off Leakage Current ^a	I _{S(off)}	V+ = 5.5 , V- = - 5.5 V		Room Full	- 2 - 15		2 15	
Switch On Leakage Ourient	I _{D(off)}	$V_{\overline{EN}} = 2.4 \text{ V}, V_D = \pm 4.5 \text{ V}, V_S = 5$	± 4.5 V	Room Full	- 2 - 15		2 15	nA
Channel On Leakage Current ^a	I _{D(on)}	V+ = 5.5 V, V- = - 5.5 V V _{EN} = 0 V, V _D = \pm 4.5 V, V _S = \pm 4.5 V		Room Full	- 2 - 15		2 15	
Digital Control								
Logic High Input Voltage	V _{INH}				2			v
Logic Low Input Voltage	V _{INL}			Full			0.8	v
Input Current ^a	I _{IN}	$V_{AX} = V_{EN} = 2 V \text{ or } 0.8 V$		Full	- 1		1	μA
Dynamic Characteristics								
Transition Time ^e	t _{TRANS}	$V_{S1} = 3.5 \text{ V}, V_{S8} = -3.5 \text{ V}, \text{ (DG}$ $V_{S1b} = 3.5 \text{ V}, V_{S4b} = -3.5 \text{ V}, \text{ (DG}$ see fig. 2		Room Full		68	89 94	
Break-Before-Make Time ^e	t _{BBM}	$V_{S(all)} = V_{DA} = 3.5 V$ see fig. 4		Room Full	1	16		ns
Enable Turn-On Time ^e	t _{ON(EN)}	V _{AX} = 0 V, V _{S1} = 3.5 V (DG94 V _{AX} = 0 V, V _{S1b} = 3.5 V (DG9	,	Room Full		68	88 94	
Enable Turn-Off Time ^e	$t_{OFF(\overline{EN})}$	see fig. 3		Room Full		58	78 81	
Source Off Capacitance ^e	C _{S(off)}	f = 1 MHz, V_S = 0 V, $V_{\overline{EN}}$ = 2 V	DG9408 DG9409	Room Room		23 23		
Drain Off Capacitance ^e	C _{D(off)}	$f = 1 \text{ MHz}, V_D = 0 \text{ V}, V_{\overline{\text{EN}}} = 2 \text{ V}$	DG9408 DG9409	Room Room		223 113		pF
Drain On Capacitance ^e	C _{D(on)}	$f = 1 \text{ MHz}, \text{ V}_{\text{D}} = 0 \text{ V}, \text{ V}_{\overline{\text{EN}}} = 0 \text{ V}$	DG9408 DG9409	Room Room		246 137		1
Power Supplies		I	2 0.0 100		1	,	1	
	l+	$V_{\overline{EN}} = V_A = 0 V \text{ or } V +$		Room			1	
Power Supply Current	I-	$v_{\rm EN} = v_{\rm A} = 0$ V OI V+		Room	- 1			μA



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		Test Conditions Unless Otherwise Specifi	ed		л	Limits 0 °C to 85	. °C	
		$V + = 5 V, \pm 10 \%, V - = 0 V$			- 40 C 10 8			
Parameter	Symbol	V_A , $V_{\overline{EN}} = 0.8$ V or 2 V ^f		Temp. ^b	Min. ^c	Typ. ^d	Max. ^c	Unit
Analog Switch					-			
Analog Signal Range ^e	V _{ANALOG}			Full	0		5	V
On-Resistance	R _{ON}	V+ = 4.5 V, V _D or V _S = 1 V or 3.5 V,	I _S = 50 mA	Room Full		7	10.5 11	
R _{ON} Match Between Channels ^g	ΔR_{ON}			Room			3.6	Ω
On-Resistance Flatness ⁱ	R _{ON} Flatness	V+ = 4.5 V, V _D = 1 V or 3.5 V, I _S =	= 50 MA	Room			9	
	I _{S(off)}	V+ = 5.5 V		Room Full	- 2 - 15		2 15	
Switch Off Leakage Current ^a	I _{D(off)}	$V_{S} = 1 V \text{ or } 4 V, V_{D} = 4 V \text{ or}$	1 V	Room Full	- 2 - 15		2 15	nA
Channel On Leakage Current ^a	I _{D(on)}	$V_{\rm H} = 5.5 \ {\rm V} \label{eq:V_D} V_{\rm D} = {\rm V}_{\rm S} = 1 \ {\rm V} \ {\rm or} \ 4 \ {\rm V}, \ {\rm sequence} \ {\rm each} \ {\rm switch} \ {\rm on}$		Room Full	- 2 - 15		2 15	
Digital Control								
Logic High Input Voltage	V _{INH}	V+ = 5 V		Full	2			v
Logic Low Input Voltage	V _{INL}			Full			0.8	, v
Input Current ^a	I _{IN}	$V_{AX} = V_{\overline{EN}} = 2 V \text{ or } 0.8 V$		Full	- 1		1	μA
Dynamic Characteristics				1		1		
Transition Time ^e	t _{TRANS}	$V_{S1} = 3.5 V$, $V_{S8} = 0 V$, (DG94 $V_{S1b} = 3.5 V$, $V_{S4b} = 0 V$, (DG9 see fig. 2		Room Full		73	94 104	ns
Break-Before-Make Time ^e	t _{OPEN}	$V_{S(all)} = V_{DA} = 3.5 V$ see fig. 4		Room Full	2	29		
Enable Turn-On Time ^e	$t_{ON(\overline{EN})}$	V _{AX} = 0 V, V _{S1} = 3.5 V (DG94 V _{AX} = 0 V, V _{S1b} = 3.5 V (DG94		Room Full		74	94 104	
Enable Turn-Off Time ^e	$t_{OFF(\overline{EN})}$	see fig. 3		Room Full		38	57 61	
Charge Injection ^e	Q	$C_L = 1 \text{ nF}, R_{GEN} = 0 \text{ , } V_{GEN} =$	0 V	Room		20		рС
Off Isolation ^{e, h}	OIRR	R _I = 1 kΩ, f = 100 kHz		Room		- 81		dB
Crosstalk ^e	X _{TALK}			Room		- 85		
Source Off Capacitance ^e	C _{S(off)}	f = 1 MHz, V_S = 0 V, $V_{\overline{EN}}$ = 0 V	DG9408 DG9409	Room Room		22 24		
Drain Off Capacitance ^e	C _{D(off)}	$f = 1 \text{ MHz}, V_D = 0 \text{ V}, V_{\overline{\text{EN}}} = 2 \text{ V}$	DG9408 DG9409	Room Room		223 113		pF
Drain On Capacitance ^e	C _{D(on)}	$f = 1 \text{ MHz}, \text{ V}_{\text{D}} = 0 \text{ V}, \text{ V}_{\overline{\text{EN}}} = 0 \text{ V}$	DG9408 DG9409	Room Room		244 143		
Power Supplies		<u> </u>					1	
Power Supply Current	l+	$V_{\overline{EN}} = V_A = 0 V \text{ or } V_+$		Room			1	μA

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		Test Conditions Unless Otherwise Specified V+ = 3 V, ± 10 %, V- = 0 V			Limits - 40 °C to 85 °C			-
Parameter	Symbol	$V_{\overline{EN}} = 0.4 \text{ V or } 1.8 \text{ V}^{\text{f}}$		Temp. ^b	Min. ^c	Typ. ^d	Max. ^c	Unit
Analog Switch	-,					-71		
Analog Signal Range ^e	V _{ANALOG}			Full	0		3	V
On-Resistance	R _{ON}	V+ = 2.7 V, V _D = 0.5 V or 2.2 V, I _S	= 5 mA	Room Full		12	25.5 26.5	
R _{ON} Match Between Channels ^g	ΔR_{ON}	V+ = 2.7 V, V _D = 0.5 V or 2.2 V, I _s	- 5 mA	Room			3.6	Ω
On- Resistance Flatness ⁱ	R _{ON} Flatness	$v + = 2.7 v, v_{\rm D} = 0.5 v \text{ or } 2.2 v, 10$	5 = 5 IIIA	Room			13	
Switch Off Leakage Current ^a	I _{S(off)}	V+ = 3.3 V		Room Full	- 2 - 15		2 15	
Switch On Leakage Current	I _{D(off)}	$V_{S} = 2 V \text{ or } 1 V, V_{D} = 1 \text{ or } 2$	V	Room Full	- 2 - 15		2 15	nA
Channel On Leakage Current ^a	I _{D(on)}	$V_{\rm H}$ = 3.3 V $V_{\rm D}$ = $V_{\rm S}$ = 1 V or 2 V, sequence each	n switch on	Room Full	- 2 - 15		2 15	
Digital Control				•				
Logic High Input Voltage	V _{INH}			Full	1.8			v
Logic Low Input Voltage	V _{INL}			Full			0.4	
Input Current ^a	I _{IN}	$V_{AX} = V_{\overline{EN}} = 1.8 \text{ V or } 0.4 \text{ V}$		Full	- 1		1	μA
Dynamic Characteristics								
Transition Time	t _{TRANS}	$V_{S1} = 1.5 V, V_{S8} = 0 V, (DG9408)$ $V_{S1b} = 1.5 V, V_{S4b} = 0 V, (DG9409)$ see fig. 2		Room Full		140	165 182	
Break-Before-Make Time	t _{BBM}	$V_{S(all)} = V_{DA} = 1.5 V$ see fig. 4		Room Full	2	63		ns
Enable Turn-On Time	$t_{ON(\overline{EN})}$	V _{AX} = 0 V, V _{S1} = 1.5 V (DG94 V _{AX} = 0 V, V _{S1b} = 1.5 V (DG94		Room Full		140	162 178	
Enable Turn-Off Time	$t_{OFF(\overline{EN})}$	see fig. 3		Room Full		76	97 104	
Charge Injection ^e	Q	$C_L = 1 \text{ nF, } R_{GEN} = 0 \text{ , } V_{GEN} =$	0 V	Room		7		рС
Off Isolation ^{e, h}	OIRR	f = 100 kHz, R _I = 1 kΩ		Room		- 81		dB
Crosstalk ^e	X _{TALK}	1 = 100 KH2, HL = 1 K32		Room		- 85		UB
Source Off Capacitance ^e	C _{S(off)}	f = 1 MHz, V _S = 0 V, V _{EN} = 1.8 V	DG9408 DG9409	Room Room		23 25		
Drain Off Capacitance ^e	C _{D(off)}	f = 1 MHz, V _D = 0 V, V _{EN} = 1.8 V	DG9408 DG9409	Room		230 120		pF
			DG9409	Room	<u> </u>	256		
Drain On Capacitance ^e	C _{D(on)}	$f = 1 \text{ MHz}, V_D = 0 \text{ V}, V_{\overline{EN}} = 0 \text{ V}$	DC0400	Doom		147		
Drain On Capacitance ^e Power Supplies	C _{D(on)}	$f = T MHZ, V_D = 0 V, V_{EN} = 0 V$	DG9409	Room		147		

Notes:

a. Leakage parameters are guaranteed by worst case test condition and not subject to production test.

b. Room = 25 °C, full = as determined by the operating temperature suffix.

c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.

d. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.

e. Guaranteed by design, not subject to production test.

f. V_{IN} = input voltage to perform proper function.

g. $\Delta R_{DON} = R_{DON} Max - R_{DON} Min.$

h. Worst case isolation occurs on Channel 4 due to proximity to the drain pin.

i. R_{DON} flatness is measured as the difference between the minimum and maximum measured values across a defined Analog signal.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

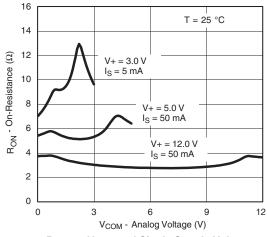
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Document Number: 71870 S13-1288-Rev. D, 27-May-13

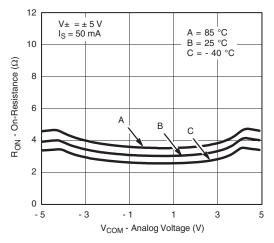


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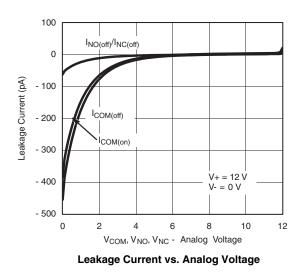
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

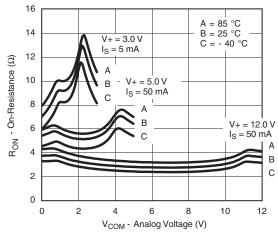


 \mathbf{R}_{ON} vs. \mathbf{V}_{COM} and Single Supply Voltage

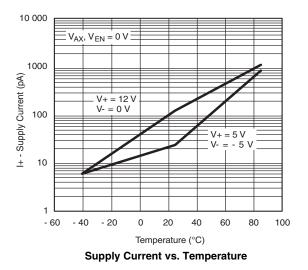


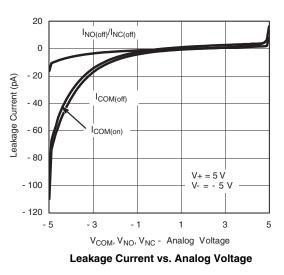
R_{ON} vs. Analog Voltage and Temperature





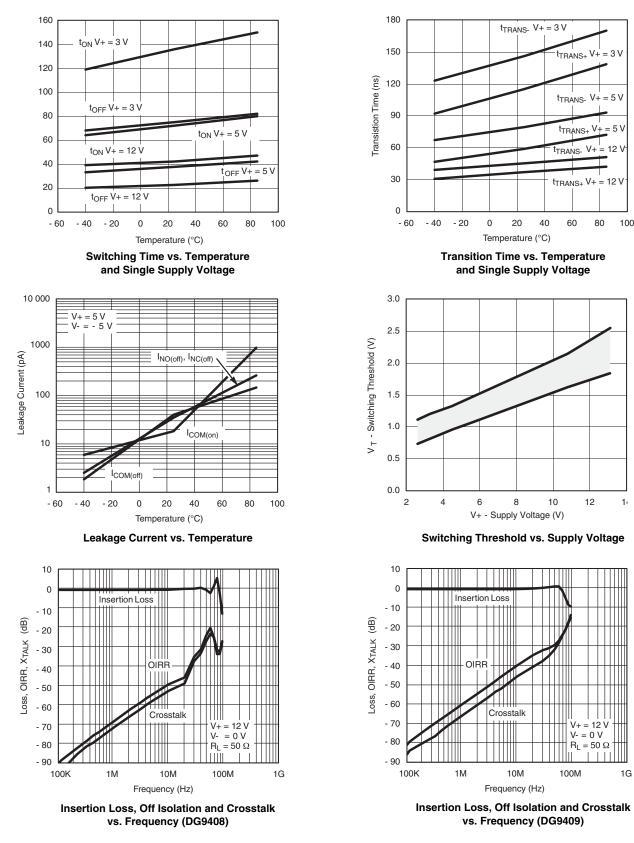
R_{ON} vs. Analog Voltage and Temperature







TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



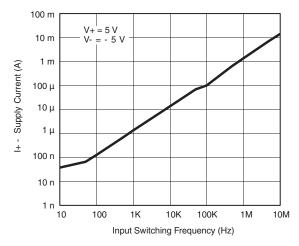
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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Supply Current vs. Input Switching Frequency

SCHEMATIC DIAGRAM (Typical Channel)

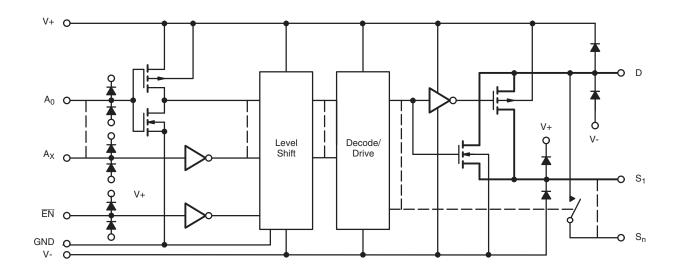
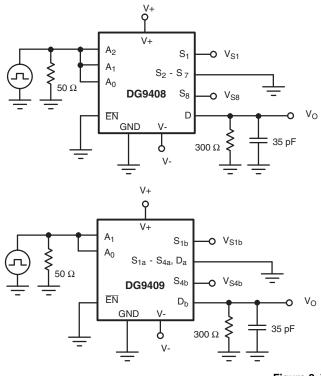
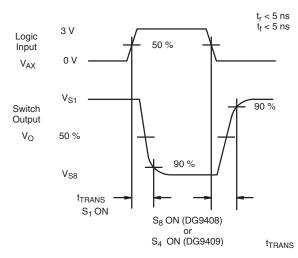


Figure 1.

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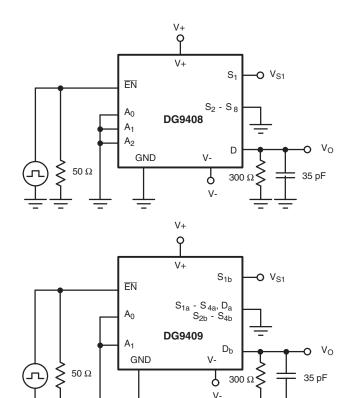
TEST CIRCUITS

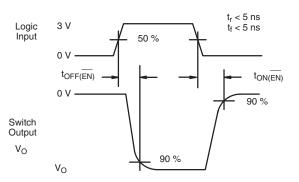




Return to Specifications: Single Supply 12 V Dual Supply V+ = 5 V, V- = - 5 V Single Supply 5 V Single Supply 3 V

Figure 2. Transition Time





Return to Specifications: Single Supply 12 V Dual Supply V+ = 5 V, V- = - 5 V Single Supply 5 V Single Supply 3 V

Figure 3. Enable Switching Time



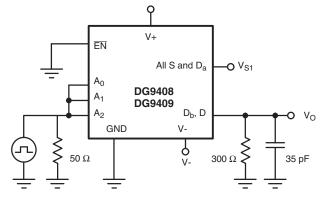
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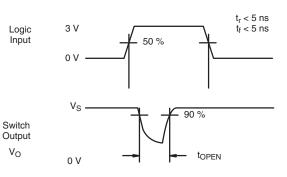
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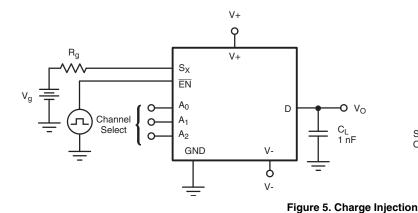


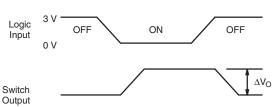


Return to Specifications: Single Supply 12 V Dual Supply V + = 5 V, V - = -5 VSingle Supply 5 V Single Supply 3 V

Figure 4. Break-Before-Make Interval

Vo





 ΔV_O is the measured voltage due to charge transfer error Q, when the channel turns off.

 $Q = C_L \ x \ \Delta V_O$

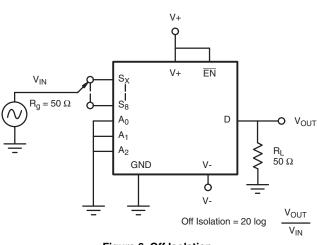
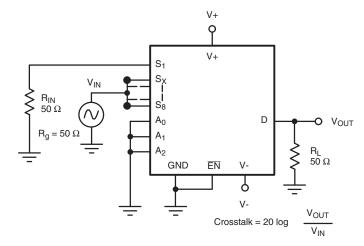


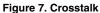
Figure 6. Off Isolation

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TEST CIRCUITS







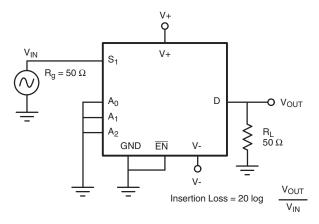


Figure 8. Insertion Loss

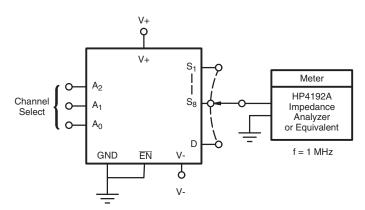


Figure 9. Source Drain Capacitance

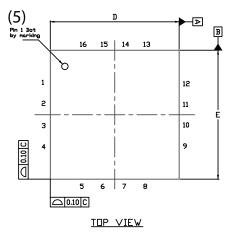
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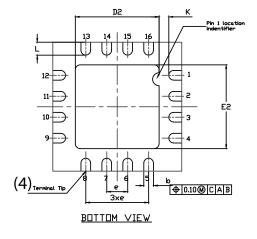
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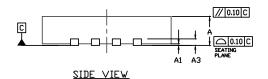
Document Number: 71870 S13-1288-Rev. D, 27-May-13



QFN 4x4-16L Case Outline







VARIATION 1 VARIATION 2 MILLIMETERS(1) MILLIMETERS(1) DIM INCHES INCHES MIN. NOM. MAX. MIN. NOM. MAX. MIN. NOM. MAX. MIN. NOM. MAX. 0.75 0.85 0.95 0.029 0.033 0.037 0.75 0.85 0.95 0.029 0.033 0.037 А 0 -0.05 0 0.002 0 0.05 _ 0.002 A1 -_ 0 A3 0.20 ref. 0.008 ref. 0.20 ref. 0.008 ref. b 0.25 0.30 0.35 0.010 0.012 0.014 0.25 0.30 0.35 0.010 0.012 0.014 4.00 BSC D 0.157 BSC 4.00 BSC 0.157 BSC 0.087 0.106 2.1 2.2 0.083 2.6 2.7 0.102 D2 2.0 0.079 2.5 0.098 0.65 BSC 0.026 BSC 0.65 BSC 0.026 BSC е Е 4.00 BSC 0.157 BSC 4.00 BSC 0.157 BSC 0.087 2.1 2.2 0.083 2.7 0.102 0.106 2.6 E2 2.0 0.079 2.5 0.098 0.20 min. 0.008 min 0.20 min. 0.008 min. Κ 0.5 0.7 0.020 0.024 0.028 0.5 0.016 0.020 L 0.6 0.3 0.4 0.012 N⁽³⁾ 16 16 16 16 Nd⁽³⁾ 4 4 4 4 Ne⁽³⁾ 4 4 4 4

Notes

⁽¹⁾ Use millimeters as the primary measurement.

⁽²⁾ Dimensioning and tolerances conform to ASME Y14.5M. - 1994.

⁽³⁾ N is the number of terminals. Nd and Ne is the number of terminals in each D and E site respectively.

⁽⁴⁾ Dimensions b applies to plated terminal and is measured between 0.15 mm and 0.30 mm from terminal tip.

⁽⁵⁾ The pin 1 identifier must be existed on the top surface of the package by using identification mark or other feature of package body.

⁽⁶⁾ Package warpage max. 0.05 mm.

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Document Number: 71921

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